

ABSTRACT

A method of manufacturing an integrated circuit having a gate structure above a substrate that includes germanium utilizes at least one layer as a seal. The layer advantageously can prevent back
5 sputtering and outdiffusion. A transistor can be formed in the substrate by doping through the layer. Another layer can be provided below the first layer. Layers of silicon dioxide, silicon carbide, silicon nitride, titanium, titanium nitride, titanium/titanium nitride, tantalum nitride, and silicon carbide can be used.